

TSMC-02-254B



April 15, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/796,891 03/09/04

Min-Hwa Chi

NEW STORAGE ELEMENT AND SRAM CELL
STRUCTURES USING VERTICAL FETS
CONTROLLED BY ADJACENT JUNCTION BIAS
THROUGH SHALLOW TRENCH ISOLATION

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on ~~July 2003~~ ^{APRIL 26, 2004} (502)

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Stephen B. Ackerman 4/26/04

U.S. Patent 6,117,722 to Wu et al., "SRAM Layout for Relaxing Mechanical Stress in Shallow Trench Isolation Technology and Method of Manufacture Thereof," describes a SRAM device and method of manufacture using dual fill STI.

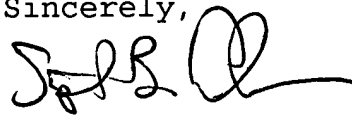
U.S. Patent 6,313,490 to Noble, "Base Current Reversal SRAM Memory Cell and Method," teaches a SRAM memory cell based on a base-current mechanism. Vertical FET device are used.

U.S. Patent 6,297,531 to Armacost et al., "High Performance, Low Power Vertical Integrated CMOS Devices," discloses a method to form vertical FET devices using epitaxial layers. A 6T SRAM cell is described in the technology.

U.S. Patent 6,137,129 to Bertin et al., "High Performance Direct Coupled FET Memory Cell," describes a method to form a latch comprising a pair of complimentary FET devices having directly coupled gates.

U.S. Patent 4,890,144 to Teng et al., "Integrated Circuit Trench Cell," discloses a vertical FET formed in a trench. A SRAM cell is disclosed.

Sincerely,

A handwritten signature in black ink, appearing to read "S. B. Ackerman", with a large, stylized "Q" or "L" at the end.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATIONS IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Specimen)

TSMC-02-254B

Application Number

10/796,891

Applicant

Min-Hwa Chi

Filing Date

03/09/04

Drawn At Unit

APR 29 2004

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	PLND DATE IF APPROPRIATE
	6117722	9/12/00	Wuu et al.	438	238	2/18/99
	6313490	11/6/01	Noble	257	288	3/16/99
	6297531	10/2/01	Armacost et al.	257	329	1/5/98
	6137129	10/24/00	Bertin et al.	257	302	1/5/98
	4890144	12/26/89	Teng et al.	357	23.4	9/14/87

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portmox Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.